

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	0	(wafer or semiconductor or substrate) and photoresist and pattern and (ion near implant\$4) and dop\$4 and organic and spacer and sidewall and (strip or remov\$4) and (pair or two or plurality or multipl\$4 or next) same ("ion implant\$4")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 08:39
S2	55	(wafer or semiconductor or substrate) and photoresist and pattern and (ion near implant\$4) and dop\$4 and organic and spacer and sidewall and (strip or remov\$4) and (pair or two or plurality or multipl\$4 or next) same implant	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 10:04
S3	0	(wafer or semiconductor or substrate) and photoresist and pattern and (ion near implant\$4) and dop\$4 and organic and spacer and sidewall and (strip or remov\$4) and (pair or two or plurality or multipl\$4 or next) same implant and (anneal or heat or thermal or cur\$4) and (UV or ultra-violet or "ultra violet") and (LDD or "lightly doped drain") and N+ and BARC and "dry etch\$4"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 08:42
S4	15	(wafer or semiconductor or substrate) and photoresist and pattern and (ion near implant\$4) and dop\$4 and organic and spacer and sidewall and (strip or remov\$4) and (pair or two or plurality or multipl\$4 or next) same implant and (anneal or heat or thermal or cur\$4) and (UV or ultra-violet or "ultra violet")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 09:46
S5	3	(wafer or semiconductor or substrate) and photoresist and pattern and (ion near implant\$4) and dop\$4 and organic and spacer and sidewall and (strip or remov\$4) and (pair or two or plurality or multipl\$4 or next) same implant and (anneal or heat or thermal or cur\$4) and (UV or ultra-violet or "ultra violet") and LDD	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 09:42

S6	0	(wafer or semiconductor or substrate) and photoresist and pattern and (ion near implant\$4) and dop\$4 and organic and spacer and sidewall and (strip or remov\$4) and (pair or two or plurality or multipl\$4 or next) same implant and (anneal or heat or thermal or cur\$4) and (UV or ultra-violet or "ultra violet") and LDD and BARC	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 08:43
S7	1	(wafer or semiconductor or substrate) and photoresist and pattern and (ion near implant\$4) and dop\$4 and organic and spacer and sidewall and (strip or remov\$4) and (pair or two or plurality or multipl\$4 or next) same implant and (anneal or heat or thermal or cur\$4) and (UV or ultra-violet or "ultra violet") and LDD and N+	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 08:44